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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuya SHIMODA et al.

Application No.: 09/892,872

Filed: June 28, 2001

Docket No.: 109975

For: FERROELECTRIC MEMORY AND METHOD OF FABRICATING THE SAME

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE ABSTRACT:

Please replace the Abstract filed with the Substitute Abstract attached hereto.

IN THE SPECIFICATION:

Please replace the specification with the Substitute Specification attached hereto.

IN THE CLAIMS:

Please replace claims 1-19 as follows:

1. (Amended) A ferroelectric memory, comprising:
- a microstructure;
 - a passive matrix array that includes memory cells formed of ferroelectric capacitors, the passive matrix array being formed on the microstructure;
 - a substrate, the microstructure being integrated on the substrate; and
 - a peripheral circuit for the passive matrix array, the peripheral circuit being formed on the substrate.

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Sub B1